

AMENDMENTS TO THE CLAIMS

The listing of claims below replace all prior versions, and listings, of claims:

- 1 1. (Original) A semiconductor device, comprising:
2 memory cells each having an area of about $6F^2$;
3 sense amplifiers;
4 bit lines coupled to the sense amplifiers in a folded bit line configuration, each bit
5 line including a first level portion and a second level portion; and
6 active area lines, transistors being formed in the active area lines and electrically
7 coupling corresponding memory cells to corresponding first level bit lines.

- 1 2. (Original) The semiconductor device of claim 1, wherein each pair of bit lines is
2 vertically twisted at one or more predetermined locations, the bit lines in the pair transitioning
3 between the first level portion and the second level portion at each twist.

- 1 3. (Original) The semiconductor device of claim 2, wherein a column pitch of each
2 memory cell is $2F$.

- 1 4. (Original) The semiconductor device of claim 1, wherein each memory cell
2 includes a capacitor formed over the first level portion of each bit line.

- 1 5. (Original) The semiconductor device of claim 4, wherein the second level portion
2 of each bit line is formed over each capacitor.

- 1 6. (Original) The semiconductor device of claim 1, wherein the bit lines extend
2 generally along the same direction as the active area lines, the bit lines intersecting the active area
3 lines at slanted portions,
4 the semiconductor device further comprising contacts between the bit lines and
5 active area lines formed in the slanted portions.

1 7. (Original) The semiconductor device of claim 6, wherein the active area lines are
2 generally straight and the bit lines extend in a wavy pattern.

1 8. (Original) The semiconductor device of claim 6, wherein the bit lines are
2 generally straight and the active area lines extend in a wavy pattern.

1 9. (Original) The semiconductor device of claim 6, each bit line having a first
2 portion on a first side of a corresponding active area line, a second portion on a second side of
3 the corresponding active area line, and a third portion on the first side of the active area line.

1 10. (Original) The semiconductor device of claim 6, wherein the bit lines extend
2 along generally the same direction as the active area lines so that the bit lines and active area
3 lines intersect at predetermined locations.

1 11. (Original) A memory device comprising:
2 memory cells each having an area of about $6F^2$;
3 sense amplifiers;
4 bit lines coupled to the sense amplifiers in a folded bit line arrangement;
5 active area lines; and
6 transistors formed in the active area lines and electrically coupling corresponding
7 memory cells to corresponding bit lines.

1 12. (Original) The memory device of claim 11, wherein each bit line has a first level
2 portion and a second level portion, each transistor electrically coupling a corresponding memory
3 cell to a first level portion of a corresponding bit line.

1 13. (Original) The memory device of claim 12, wherein each pair of bit lines is
2 vertically twisted at one or more predetermined locations, the bit lines in the pair transitioning
3 between the first level portion and the second level portion at each twist.

1 14. (Original) The memory device of claim 12, wherein each memory cell includes a
2 capacitor formed over the first level portion of each bit line.

1 15. (Original) The memory device of claim 14, wherein the second level portion of
2 each bit line is formed over each capacitor.

1 16. (Original) The memory device of claim 11, wherein the bit lines extend generally
2 along the same direction as the active area lines, the bit lines intersecting the active area lines at
3 slanted portions.

1 17. (Original) The memory device of claim 11, wherein each pair of bit lines is
2 coupled to one side of a corresponding sense amplifier.

1 18. (Original) A method of making a memory device, comprising:
2 forming memory cells each having an area of about $6F^2$;
3 forming sense amplifiers;
4 coupling bit lines to the sense amplifiers in a folded bit line arrangement;
5 forming transistors in active area lines; and
6 the transistors electrically coupling corresponding memory cells to corresponding
7 bit lines.

1 19. (Currently Amended) ~~The method of claim 18, further comprising:~~ A method of
2 making a memory device, comprising:
3 forming memory cells each having an area of about $6F^2$;
4 forming sense amplifiers;
5 coupling bit lines to the sense amplifiers in a folded bit line arrangement;
6 forming transistors in active area lines;
7 the transistors electrically coupling corresponding memory cells to corresponding
8 bit lines;
9 forming each bit line of a first level portion and a second level portion; and

10 coupling each transistor to the first level portion of the corresponding bit line.

1 20. (Original) The method of claim 19, further comprising:
2 vertically twisting each pair of bit lines at one or more predetermined locations;
3 and
4 transitioning the bit lines in the pair between the first level portion and the second
5 level portion at each twist.

1 21. (Original) The method of claim 20, further comprising forming a capacitor of each
2 memory cell over the first level portion of each bit line.

1 22. (Original) The method of claim 21, further comprising forming the second level
2 portion of each bit line over the capacitor.

1 23. (Previously Presented) The semiconductor device of claim 1, wherein in the
2 folded bit line arrangement a pair of bit lines is coupled to a same side of each corresponding
3 sense amplifier.

1 24. (Previously Presented) The memory device of claim 11, wherein in the folded bit
2 line arrangement a pair of bit lines is coupled to a same side of each corresponding sense
3 amplifier.

1 25. (Previously Presented) The method of claim 18, wherein coupling the bit lines to
2 the sense amplifiers in the folded bit line arrangement comprises coupling each pair of bit lines to
3 a same side of each corresponding sense amplifier.